

**AMENDMENTS TO THE SPECIFICATION**

Please **REPLACE** **ABSTRACT OF DISCLOSURE** on page 49 with the followings:

**ABSTRACT OF DISCLOSURE**

A method of forming a TFT substrate panel uses less steps of photolithography. A gate layer is deposited on an insulating substrate and is patterned into a gate electrode and a gate pad. A gate insulating layer, a semiconductor layer, an ohmic contact layer and a conductor layer are sequentially formed on top of the gate layer. The sequentially laid four layers are patterned to form a data electrode. A passivation layer is formed on it and goes through one step photolithography process using a mask that has different light transmissivity. Using the mask with different thickness, gate pad area, data pad area and a contact hole for a pixel electrode can be formed at the same time in one photolithography step.